



Features

Environments

High Conversion Efficiency

80V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Rated to +175°C - Ideal for High Ambient Temperature

Ensures More Reliable and Robust End Application

Lead-Free Finish; RoHS Compliant (Notes 1 & 2) Halogen and Antimony Free. "Green" Device (Note 3)

contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

 $\label{eq:low-RDS(ON)} Low \; R_{\text{DS(ON)}} - \text{Minimizes On-State Losses}$

100% Unclamped Inductive Switching (UIS) Test in Production -

For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable,

and manufactured in IATF 16949 certified facilities), please

Product Summary

BV _{DSS}	Rds(on)	I _D Tc = +25°C (Note 5)
80V	$4m\Omega$ @ $V_{GS} = 10V$	100A

Description and Applications

This new generation MOSFET is designed to minimize R_{DS(ON)} yet maintain superior switching performance. This device is ideal for use in power management and load switch.

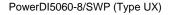
- DC-DC converters
- Load switches

Mechanical Data

- Package: PowerDI®5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3

 $s \square$

Weight: 0.097 grams (Approximate)



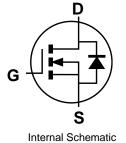








Bottom View



s [sП GΠ Top View

Pin Configuration

Пο

Пο

ΠD

Пο

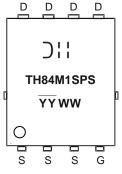
Ordering Information (Note 4)

Part Number	Dockers	Packing		
Part Number	Package	Qty.	Carrier	
DMTH84M1SPSW-13	PowerDI5060-8/SWP (Type UX)	2500	Tape & Reel	

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/
- 5. Package limited.

Marking Information



⊃¦¦= Manufacturer's Marking TH84M1SPS = Product Type Marking Code YYWW = Date Code Marking \overline{YY} = Year (ex: 24 = 2024) WW = Week (01 to 53)



Maximum Ratings (@T_C = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	VDSS	80	V
Gate-Source Voltage	V_{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V (Note 8)	lo	100 100	А
Maximum Continuous Body Diode Forward Current (Not	Is	83	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	lрм	400	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty 0	lsм	400	Α
Avalanche Current, L = 1mH (Note 9)	I _{AS}	23	Α
Avalanche Energy, L = 1mH (Note 9)	Eas	264.5	mJ

Thermal Characteristics ($@T_C = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 6)	T _A = +25°C	PD	1.6	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	RθJA	96	°C/W
Total Power Dissipation (Note 7)	T _A = +25°C	Pp	2.8	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	$R_{\theta JA}$	53	°C/W
Total Power Dissipation (Note 8)	T _C = +25°C	Pp	136	W
Thermal Resistance, Junction to Case (Note 8)		R _θ JC	1.1	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

Electrical Characteristics (@T_C = +25°C, unless otherwise specified.)

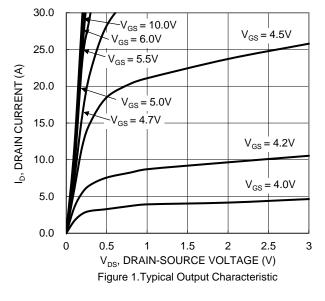
Observatoristis	0	B.4.*	T	M	11!4	Table Oan did an	
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 10)	1	1		1			
Drain-Source Breakdown Voltage	BV _{DSS}	80	_	_	V	$V_{GS} = 0$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μΑ	$V_{DS} = 64V, V_{GS} = 0$	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0$	
ON CHARACTERISTICS (Note 10)							
Gate Threshold Voltage	V _{GS(TH)}	2	-	4	٧	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	Descour	_	3.1	4	mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Drain-Source Off-Resistance	RDS(ON)	_	4.4	5.7	11122	$V_{GS} = 6V$, $I_D = 20A$	
Diode Forward Voltage	VsD	_	0.8	1.2	V	V _G S = 0, I _S = 20A	
DYNAMIC CHARACTERISTICS (Note 11)							
Input Capacitance	Ciss	_	4209	_		V _{DS} = 40V, V _{GS} = 0, f = 1MHz	
Output Capacitance	Coss	_	1513	_	pF		
Reverse Transfer Capacitance	Crss	_	62	_			
Gate Resistance	R_g	_	2.2	_	Ω	$V_{DS} = 0$, $V_{GS} = 0$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 6V)	Qg	_	41	_			
Total Gate Charge (V _{GS} = 10V)	Qg	_	63	_	nC	V _{DS} = 40V. I _D = 20A	
Gate-Source Charge	Qgs	_	17	_	IIC	VDS = 40V, ID = 20A	
Gate-Drain Charge	Q_{gd}	_	16	_			
Turn-On Delay Time	t _{D(ON)}	_	16	_			
Turn-On Rise Time	t _R	_	24	_	20	$V_{DD} = 40V, V_{GS} = 10V,$	
Turn-Off Delay Time	tD(OFF)	_	53	_	ns	$I_D = 20A$, $R_G = 6\Omega$	
Turn-Off Fall Time	t _F	_	31	_			
Body Diode Reverse-Recovery Time	trr	_	56	_	ns	1- 20A di/dt 400A/v-	
Body Diode Reverse-Recovery Charge	Qrr	_	100	_	nC	Is = 20A, di/dt = 100A/μs	

Notes:

- 5. Package limited.
- 6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

 8. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 9. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
- 10. Short duration pulse test used to minimize self-heating effect.
- 11. Guaranteed by design. Not subject to product testing.





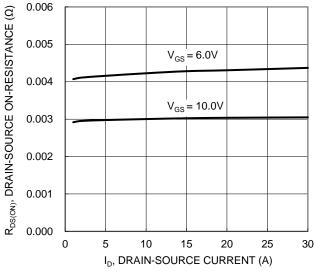


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

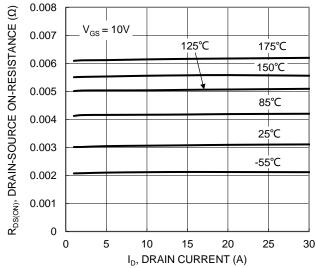
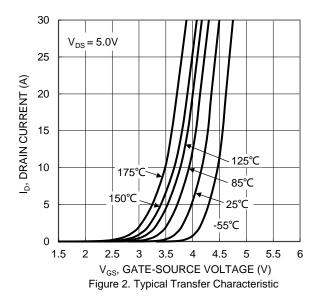
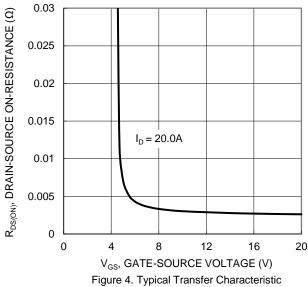


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





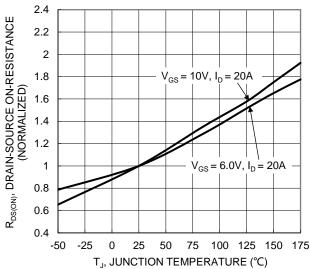


Figure 6. On-Resistance Variation with Temperature



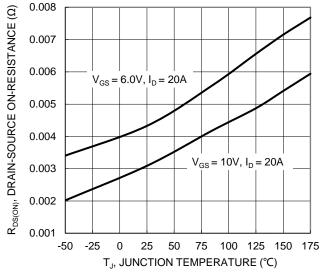
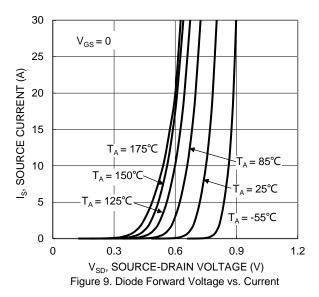
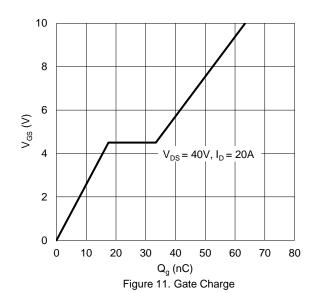


Figure 7. On-Resistance Variation with Temperature





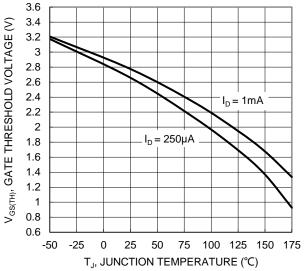
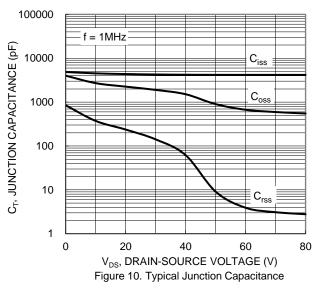
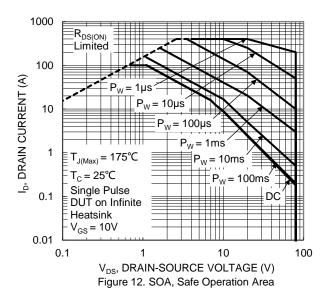


Figure 8. Gate Threshold Variation vs. Junction Temperature







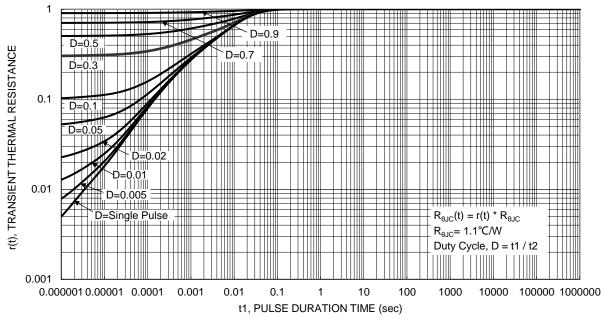


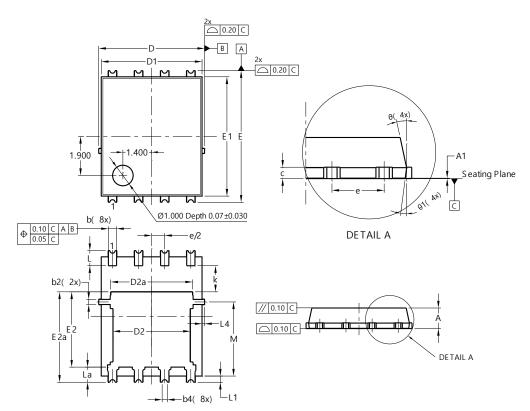
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8/SWP (Type UX)

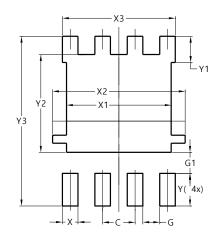


PowerDI5060-8/SWP					
(Type UX)					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0	0.05			
b	0.30	0.50	0.41		
b2	0.20	0.35	0.25		
b4	().25REF	=		
С	0.230	0.330	0.277		
D	5	.15 BS0	3		
D1	4.70	5.10	4.90		
D2	3.56	3.96	3.76		
D2a	3.78	4.18	3.98		
E	6	.40 BS0	2		
E1	5.60	6.00	5.80		
E2	3.46	3.86	3.66		
E2a	4.195	4.595	4.395		
е	1.27BSC				
k	1.05				
L	0.635	0.835	0.735		
La	0.635	0.835	0.735		
L1	0.200	0.400	0.300		
L4	0.025	0.225	0.125		
M	3.205	4.005	3.605		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8/SWP (Type UX)



Dimensions	value		
פווטופווסוווט	(in mm)		
С	1.270		
G	0.660		
G1	0.820		
X	0.610		
X1	4.100		
X2	5.190		
Х3	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		

Value



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